

STARPOWER

SEMICONDUCTOR

IGBT

GD35FSY120L2S

1200V/35A 6 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

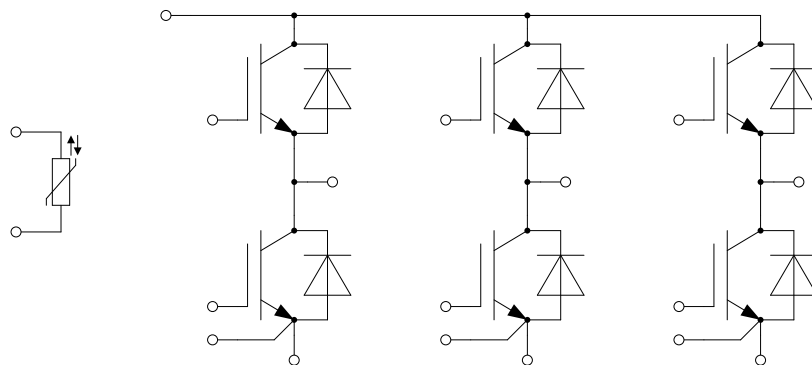
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- Low switching loss
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Fast & soft reverse recovery anti-parallel FWD
- Isolated heatsink using DBC technology

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT-inverter**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	70	A
	@ $T_C=100^{\circ}\text{C}$	35	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	70	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	301	W

Diode-inverter

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	35	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	70	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	2500	V

IGBT-inverter Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=35\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		1.70	2.15	V	
		$I_C=35\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		1.95			
		$I_C=35\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		2.00			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=0.88\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.2	6.0	6.8	V	
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			1.0	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			100	nA	
R_{Gint}	Internal Gate Resistance			0		Ω	
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		3.62		nF	
C_{res}	Reverse Transfer Capacitance				0.10		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		0.27		μC	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=35\text{A}, R_G=12\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		27		ns	
t_r	Rise Time			14		ns	
$t_{d(off)}$	Turn-Off Delay Time			247		ns	
t_f	Fall Time			118		ns	
E_{on}	Turn-On Switching Loss			2.03		mJ	
E_{off}	Turn-Off Switching Loss			2.06		mJ	
$t_{d(on)}$	Turn-On Delay Time		$V_{CC}=600\text{V}, I_C=35\text{A}, R_G=12\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		27		ns
t_r	Rise Time				17		ns
$t_{d(off)}$	Turn-Off Delay Time			304		ns	
t_f	Fall Time			175		ns	
E_{on}	Turn-On Switching Loss			3.10		mJ	
E_{off}	Turn-Off Switching Loss			2.99		mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=35\text{A}, R_G=12\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$			27		ns
t_r	Rise Time				19		ns
$t_{d(off)}$	Turn-Off Delay Time			319		ns	
t_f	Fall Time			206		ns	
E_{on}	Turn-On Switching Loss			3.37		mJ	
E_{off}	Turn-Off Switching Loss			3.30		mJ	
I_{SC}	SC Data		$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		140		A

Diode-inverter Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=35\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		2.20	2.65	V
		$I_F=35\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		2.30		
		$I_F=35\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		2.25		
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=35\text{A},$ $-di/dt=1155\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		2.09		μC
I_{RM}	Peak Reverse Recovery Current			47		A
E_{rec}	Reverse Recovery Energy			1.11		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=35\text{A},$ $-di/dt=1155\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		3.41		μC
I_{RM}	Peak Reverse Recovery Current			56		A
E_{rec}	Reverse Recovery Energy			2.61		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=35\text{A},$ $-di/dt=1155\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^\circ\text{C}$		3.85		μC
I_{RM}	Peak Reverse Recovery Current			58		A
E_{rec}	Reverse Recovery Energy			3.05		mJ

NTC Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated Resistance			5.0		k Ω
$\Delta R/R$	Deviation of R_{100}	$T_C=100^\circ\text{C}, R_{100}=493.3\Omega$	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K
$B_{25/80}$	B-value	$R_2=R_{25}\exp[B_{25/80}(1/T_2-1/(298.15\text{K}))]$		3411		K
$B_{25/100}$	B-value	$R_2=R_{25}\exp[B_{25/100}(1/T_2-1/(298.15\text{K}))]$		3433		K

Module Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		25		nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		4.50		m Ω
R_{thJC}	Junction-to-Case (per IGBT-inverter)		0.453	0.498	K/W
	Junction-to-Case (per Diode-inverter)		0.786	0.865	
R_{thCH}	Case-to-Heatsink (per IGBT-inverter)		0.548		K/W
	Case-to-Heatsink (per Diode-inverter)		0.952		
	Case-to-Heatsink (per Module)		0.058		
F	Mounting Force Per Clamp	20		50	N
G	Weight of Module		24		g

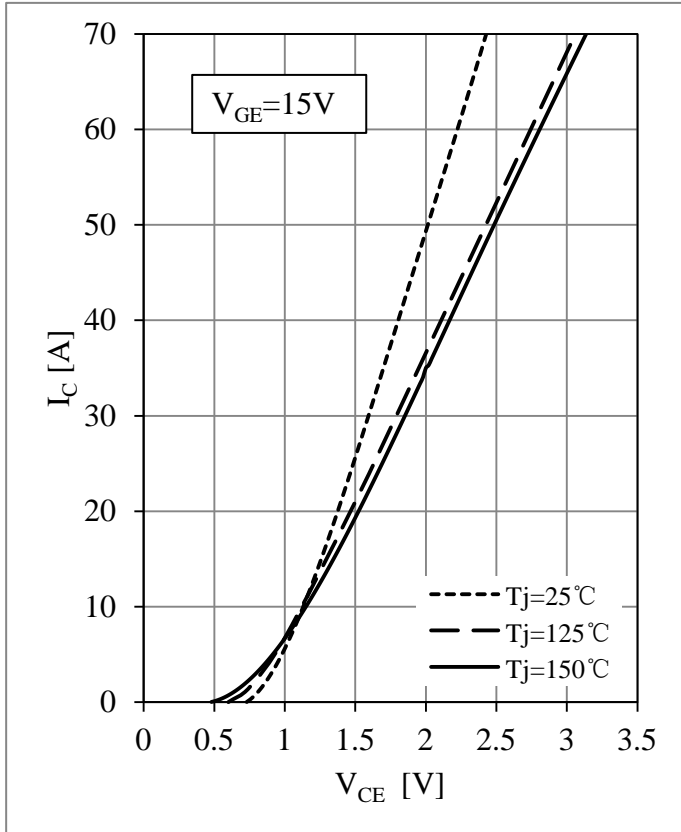


Fig 1. IGBT-inverter Output Characteristics

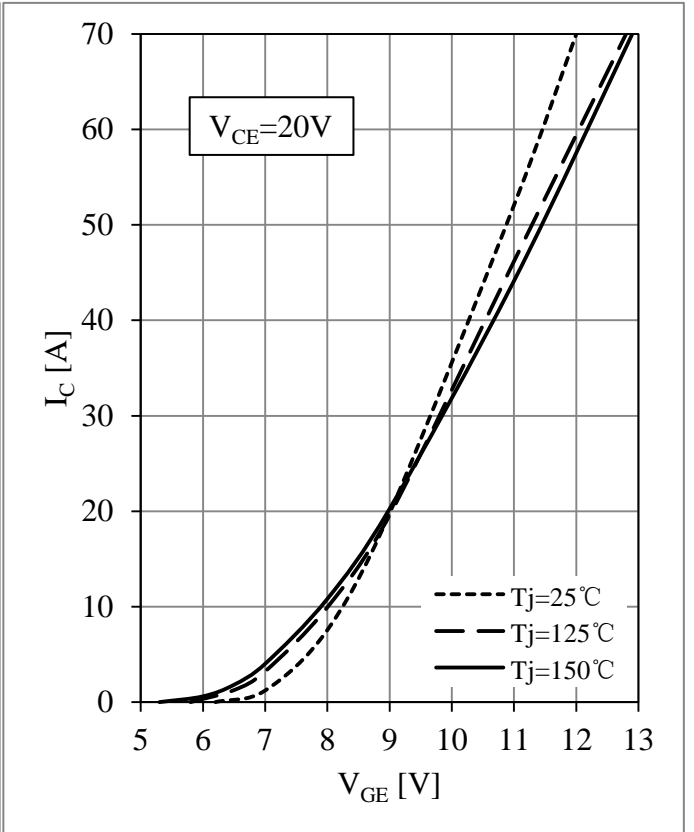


Fig 2. IGBT-inverter Transfer Characteristics

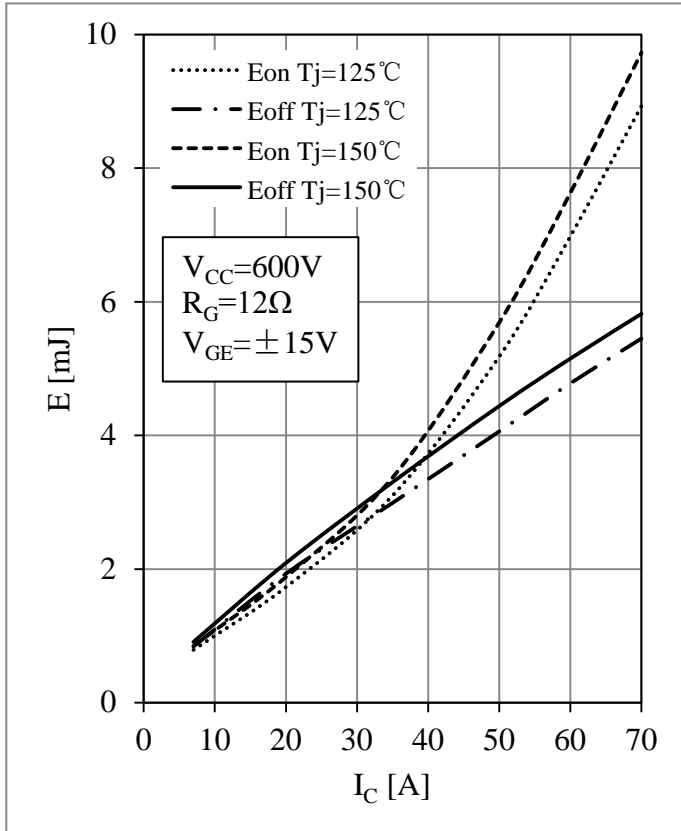


Fig 3. IGBT-inverter Switching Loss vs. I_C

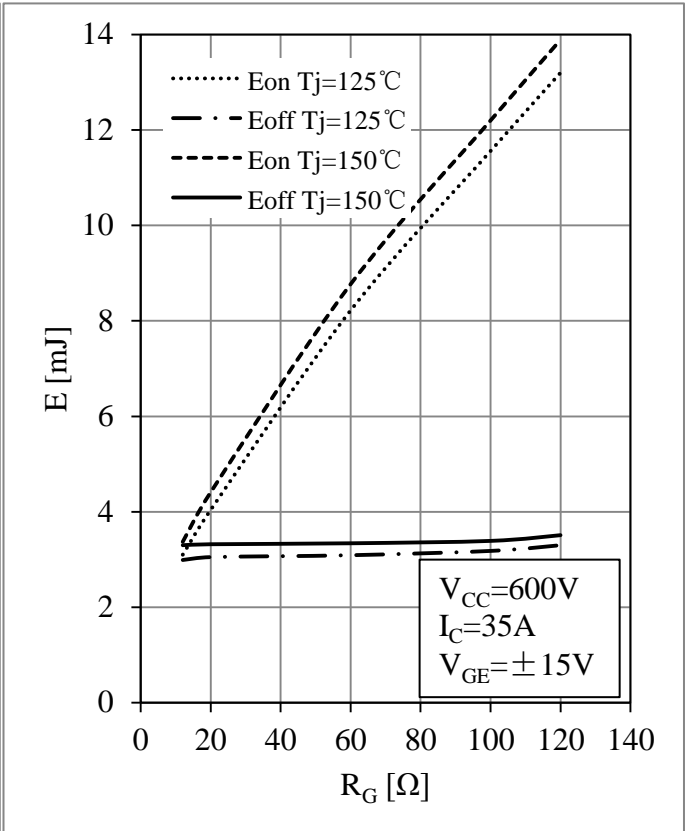


Fig 4. IGBT-inverter Switching Loss vs. R_G

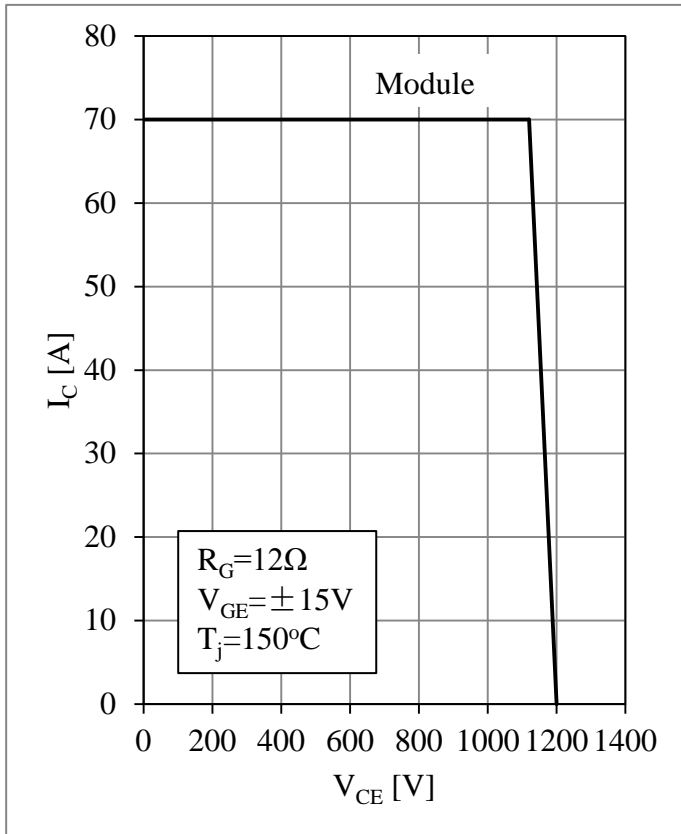


Fig 5. IGBT-inverter RBSOA

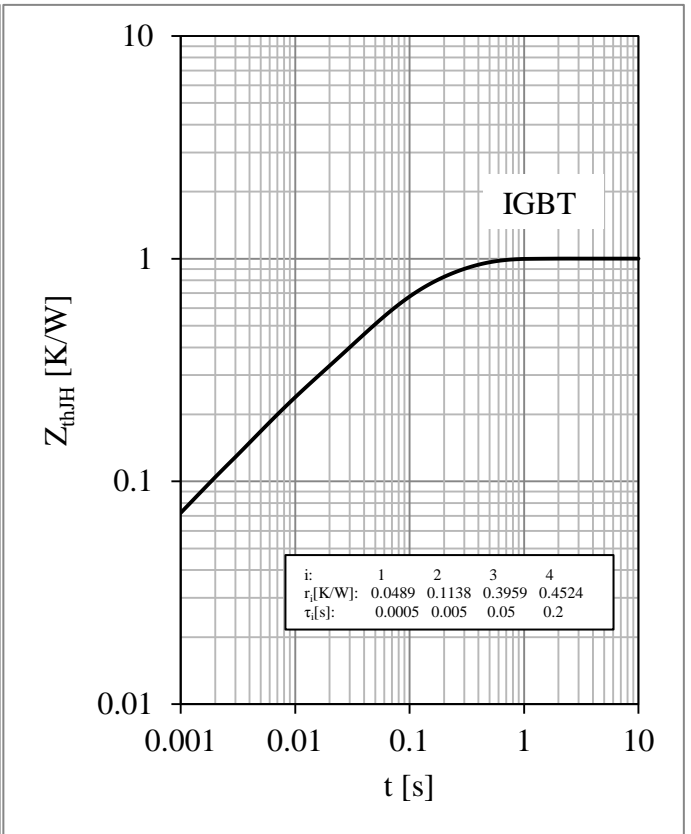


Fig 6. IGBT-inverter Transient Thermal Impedance

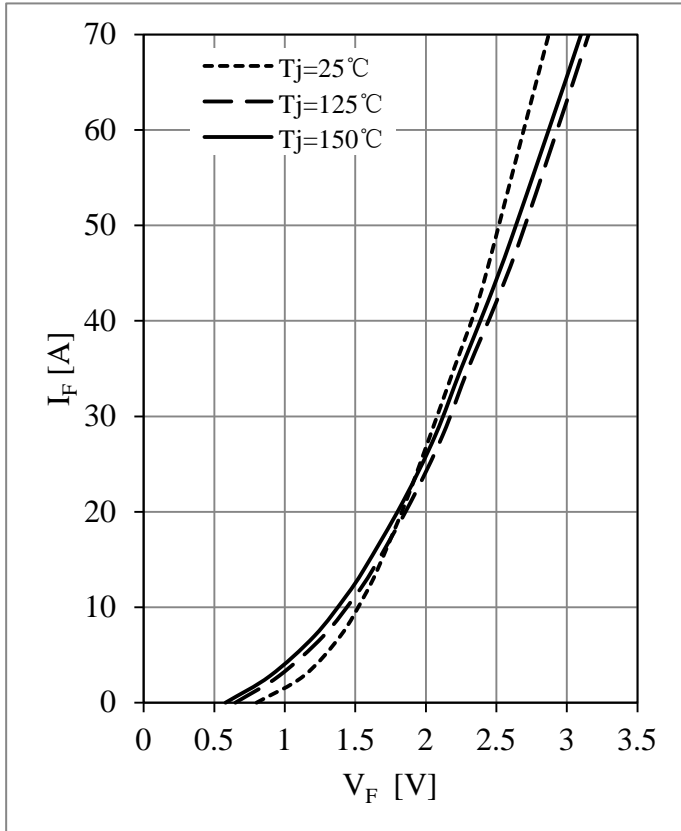


Fig 7. Diode-inverter Forward Characteristics

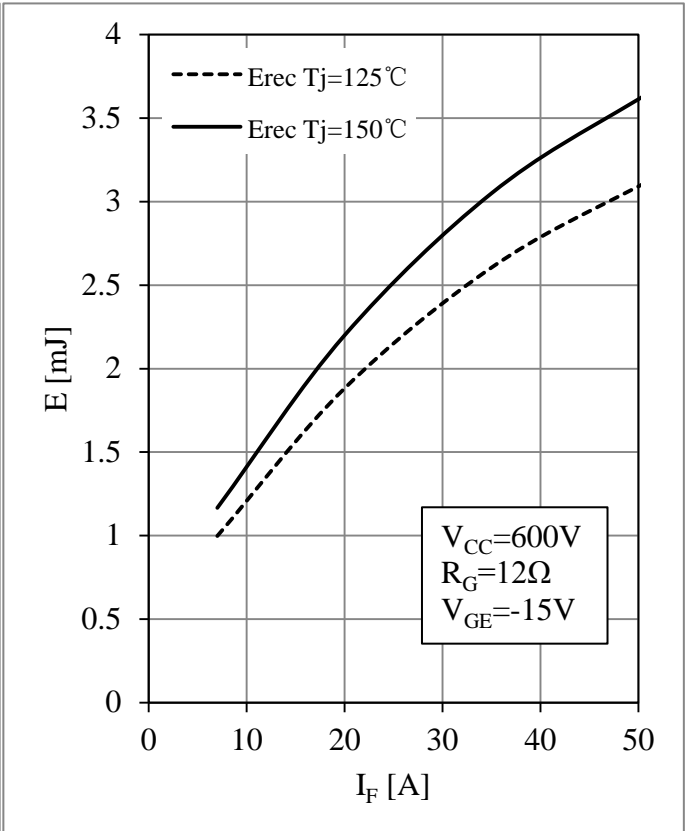


Fig 8. Diode-inverter Switching Loss vs. I_F

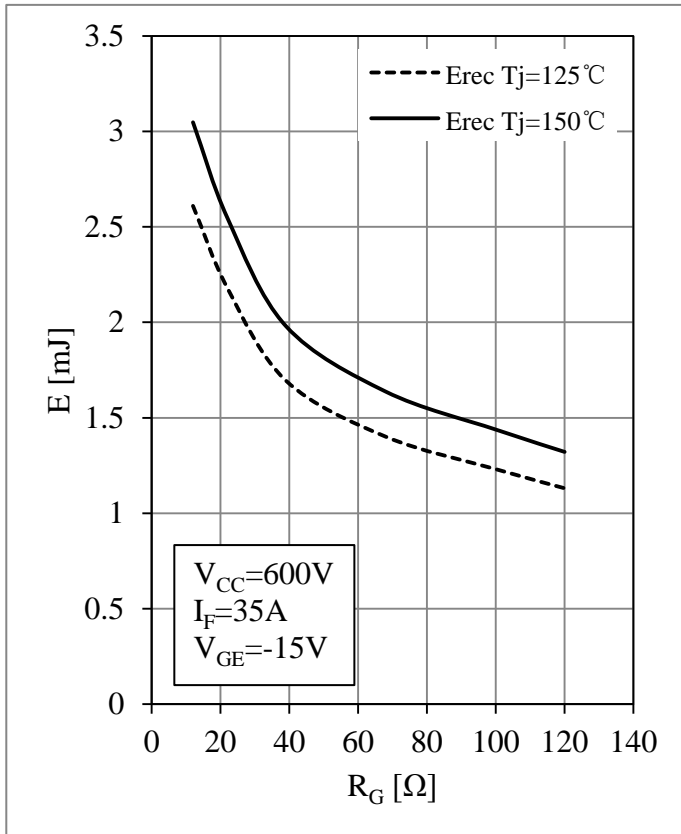


Fig 9. Diode-inverter Switching Loss vs. R_G

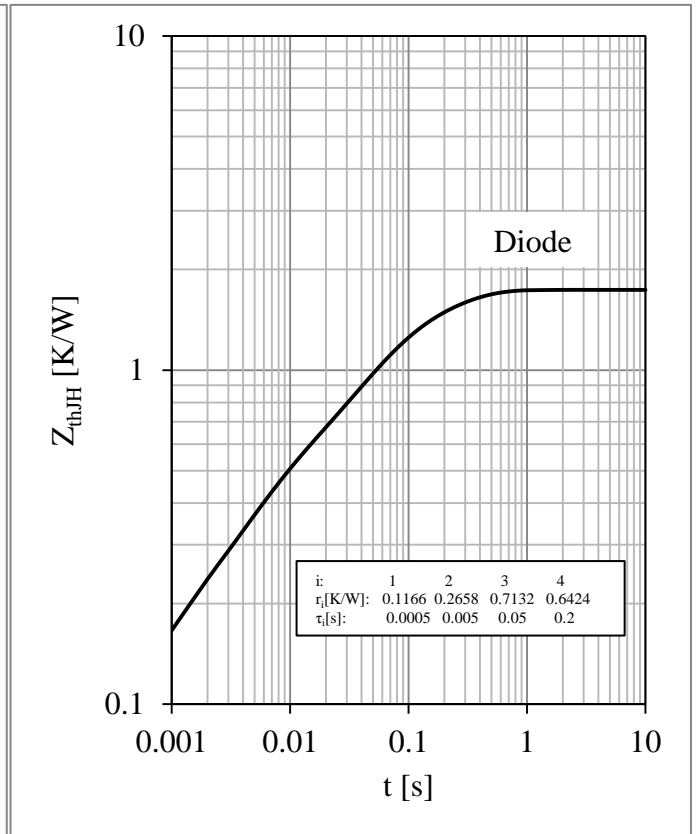


Fig 10. Diode-inverter Transient Thermal Impedance

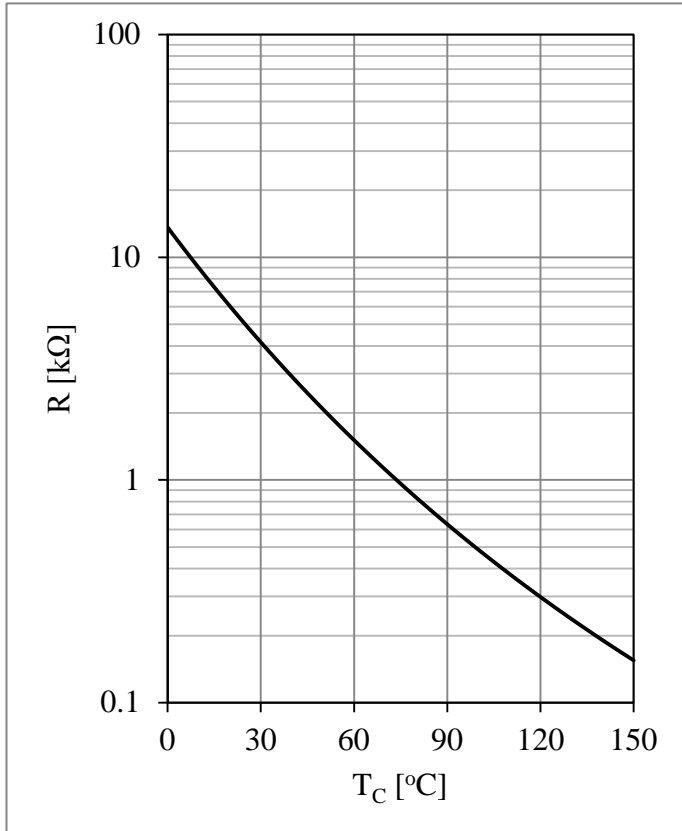
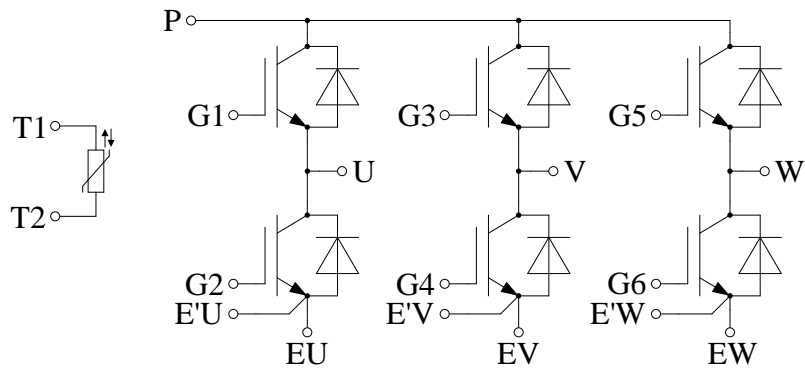


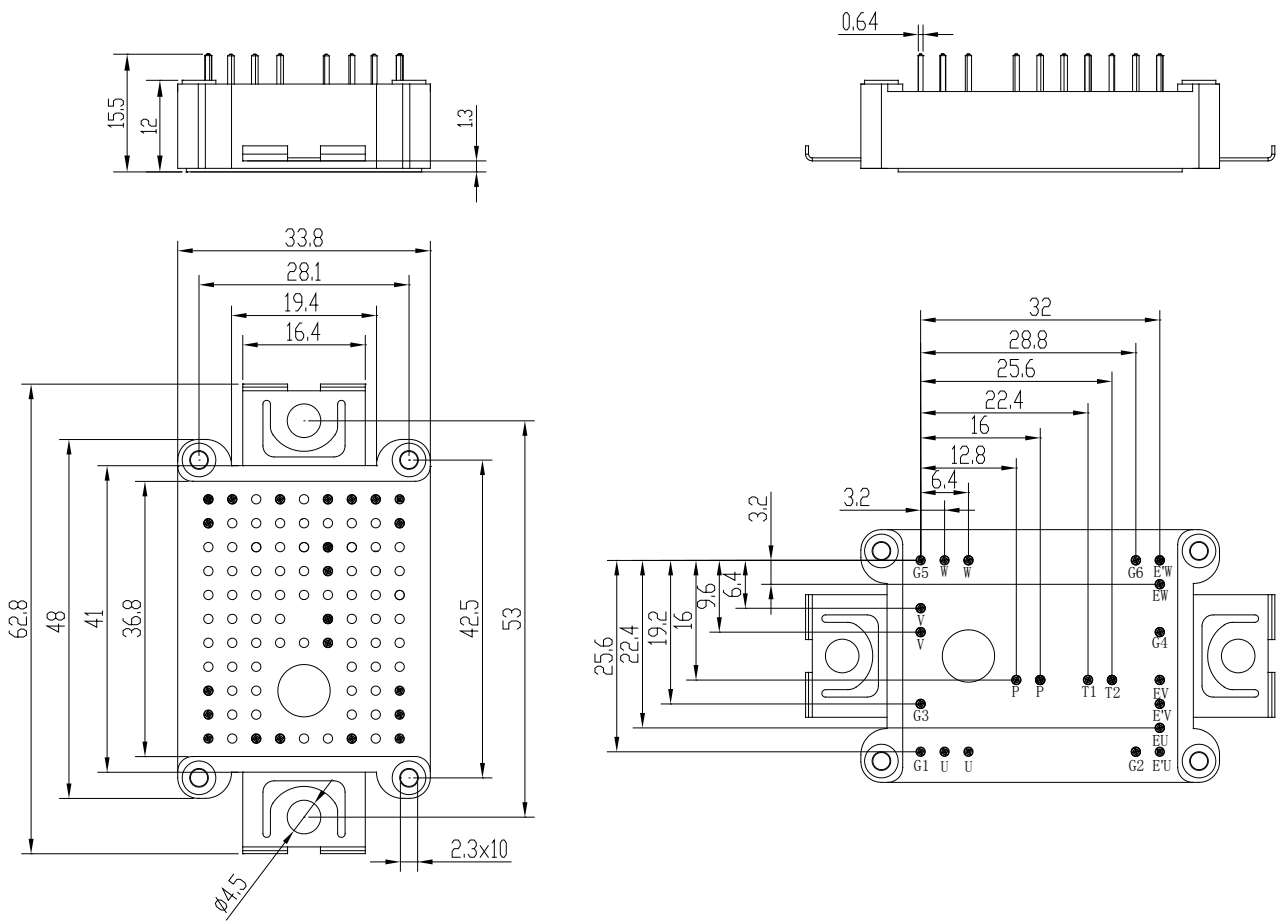
Fig 11. NTC Temperature Characteristic

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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